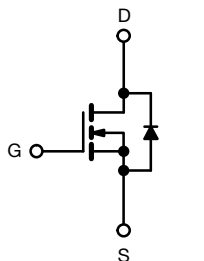
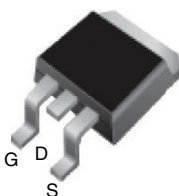


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	1.2
Q_g max. (nC)	42	
Q_{gs} (nC)	10	
Q_{gd} (nC)	20	
Configuration	Single	

D²PAK (TO-263)

N-Channel MOSFET

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C_{oss} specified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.



RoHS*
Available
HALOGEN
FREE
Available

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Single transistor forward

ORDERING INFORMATION

Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHFBC40AS-GE3	SiHFBC40ASTRL-GE3 ^a	SiHFBC40ASTRR-GE3 ^a
Lead (Pb)-free	IRFBC40ASPbF	IRFBC40ASTRLPbF ^a	IRFBC40ASTRRPbF ^a
	SiHFBC40AS-E3	SiHFBC40ASTL-E3 ^a	SiHFBC40ASTR-E3 ^a

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ^e	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	A
		$T_C = 100\text{ }^{\circ}\text{C}$	
Pulsed Drain Current ^{a, e}	I_{DM}	25	
Linear Derating Factor		1.0	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ^b	E_{AS}	570	mJ
Repetitive Avalanche Current ^a	I_{AR}	6.2	A
Repetitive Avalanche Energy ^a	E_{AR}	13	mJ
Maximum Power Dissipation	P_D	125	W
Peak Diode Recovery dV/dt ^{c, e}	dV/dt	6.0	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Soldering Recommendations (Peak temperature) ^d	for 10 s	300	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 29.6\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 6.2\text{ A}$ (see fig. 12).
- $I_{SD} \leq 6.2\text{ A}$, $dI/dt \leq 88\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$.
- 1.6 mm from case.
- Uses IRFBC40A, SiHFBC40A data and test conditions.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

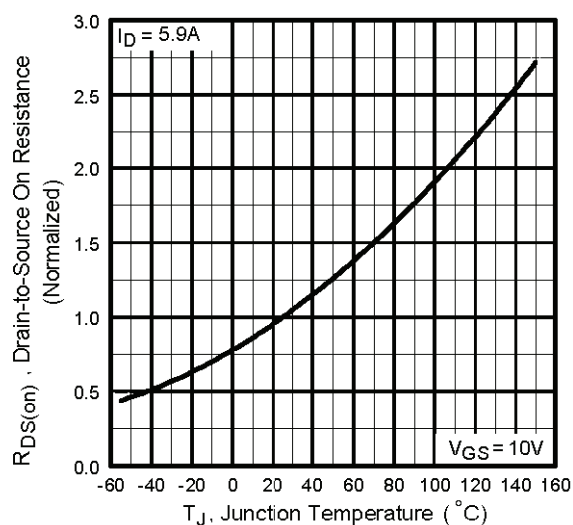
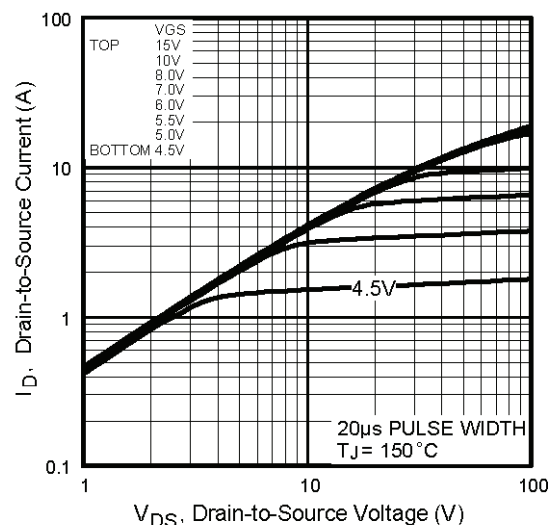
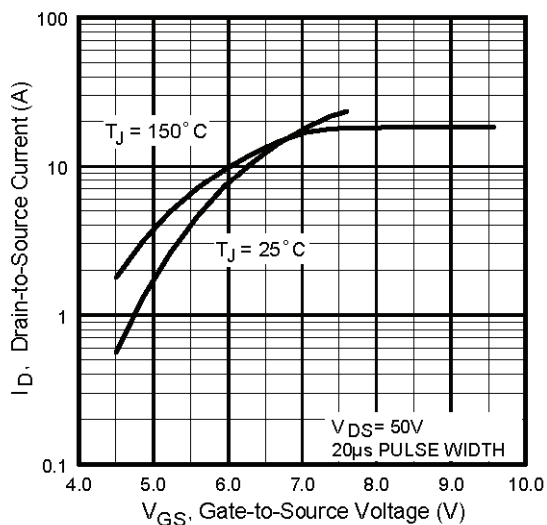
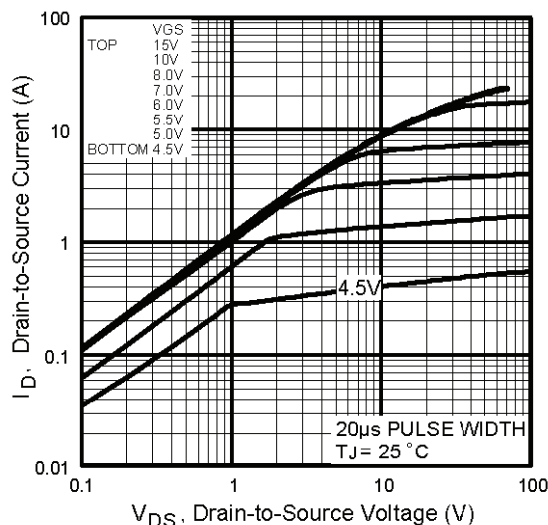
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$ ^d	-	0.66	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 480\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 3.7\text{ A}$ ^b	-	-	1.2	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 3.7\text{ A}$	3.4	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	1036	-	pF
Output Capacitance	C_{oss}		-	136	-	
Reverse Transfer Capacitance	C_{rss}		-	7.0	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 1.0\text{ V}$, $f = 1.0\text{ MHz}$ $V_{DS} = 480\text{ V}$, $f = 1.0\text{ MHz}$ $V_{DS} = 0\text{ V}$ to 480 V ^c	-	1487	-	
Output Capacitance Effective	$C_{oss\text{ eff.}}$		-	48	-	nC
Total Gate Charge	Q_g		-	-	42	
Gate-Source Charge	Q_{gs}	$V_{GS} = 10\text{ V}$ $I_D = 6.2\text{ A}$, $V_{DS} = 480\text{ V}$, see fig. 6 and 13 ^b	-	-	10	
Gate-Drain Charge	Q_{gd}		-	-	20	ns
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}$, $I_D = 6.2\text{ A}$, $R_g = 9.1\text{ }\Omega$, $R_D = 47\text{ }\Omega$, see fig. 10 ^b	-	13	-	
Rise Time	t_r		-	23	-	
Turn-Off Delay Time	$t_{d(off)}$		-	31	-	
Fall Time	t_f		-	18	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	0.6	-	3.9	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	6.2	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	25	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 6.2\text{ A}$, $V_{GS} = 0\text{ V}$ ^b	-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = 6.2\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$ ^b	-	431	647	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.8	2.8	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

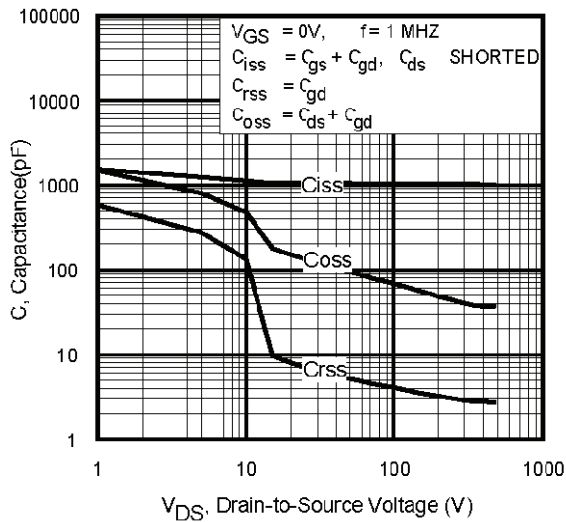
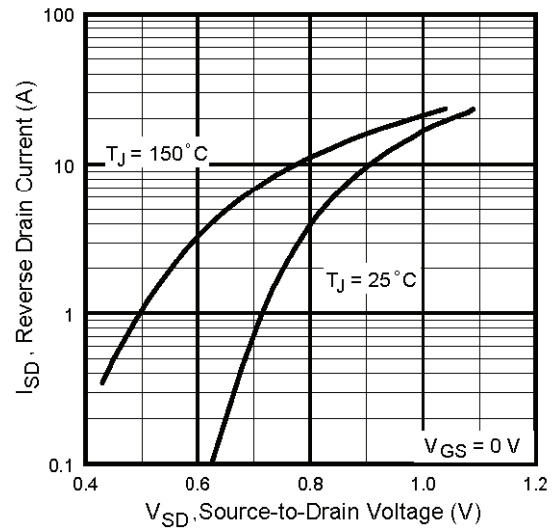
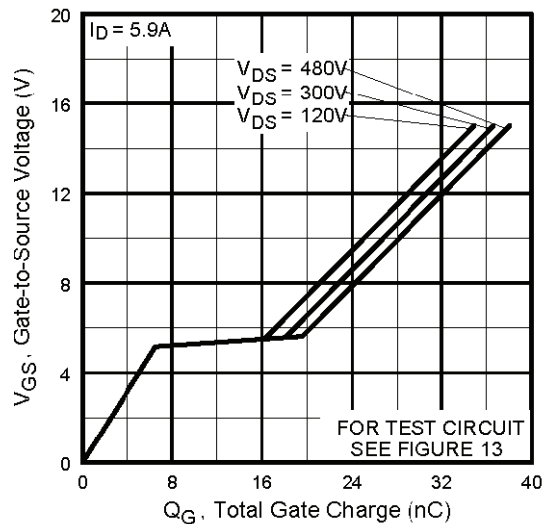
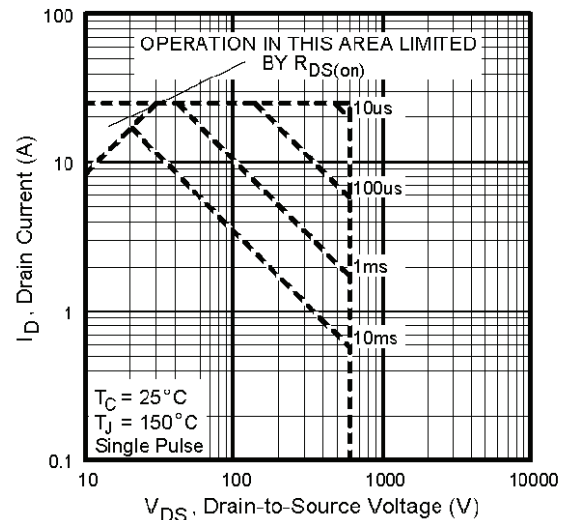
Notes

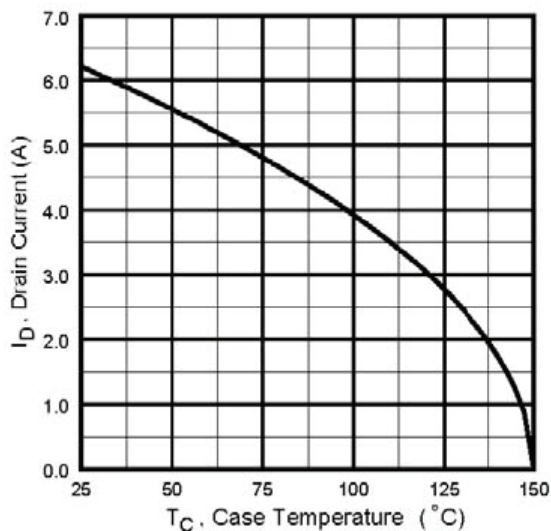
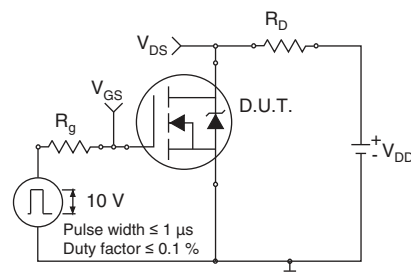
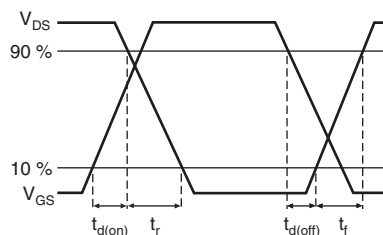
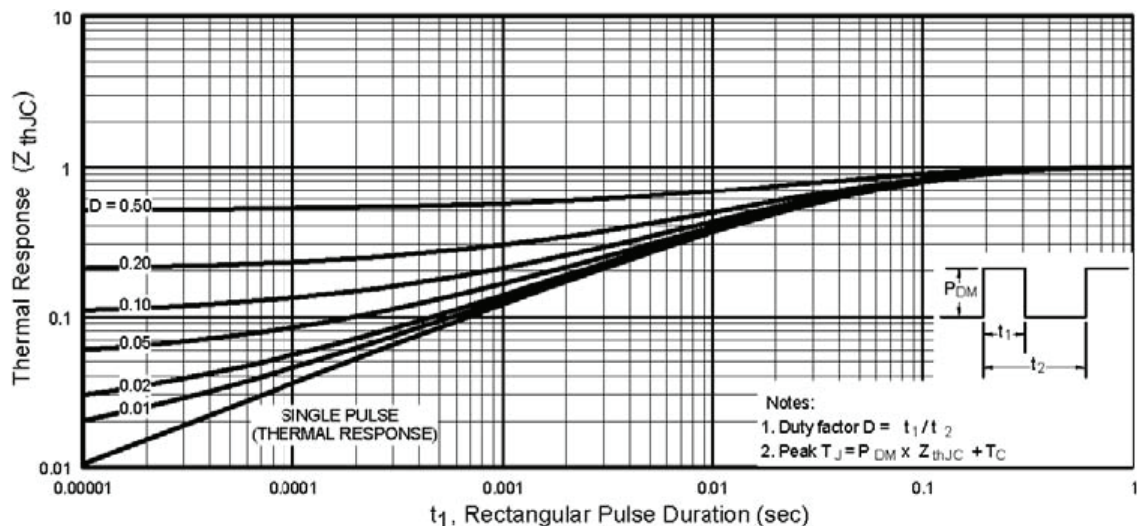
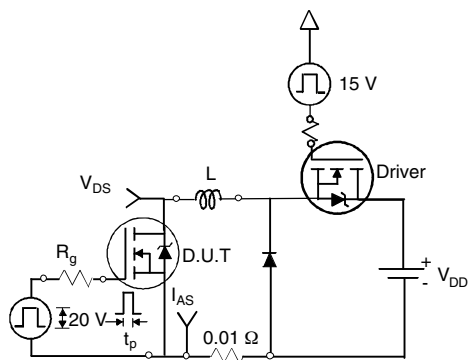
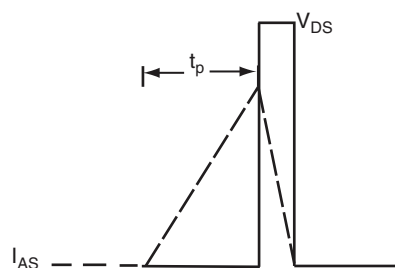
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
d. Uses IRHFBC40A, SiHFBC40A data and test conditions.

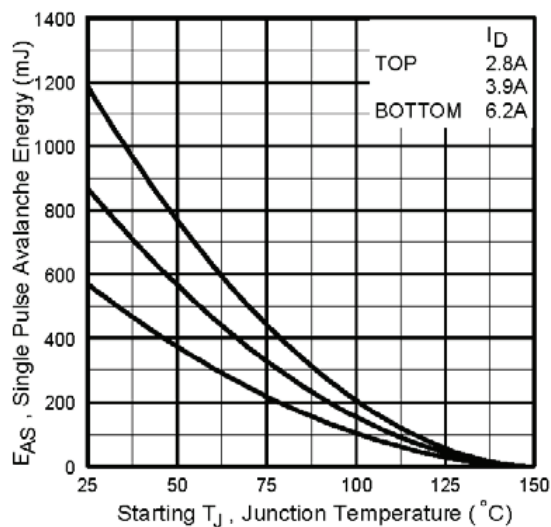
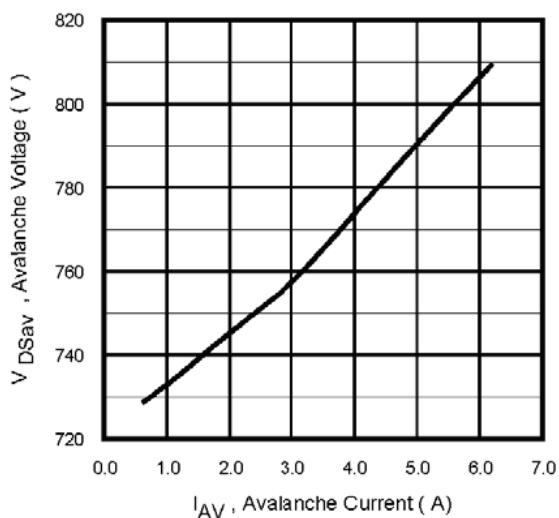
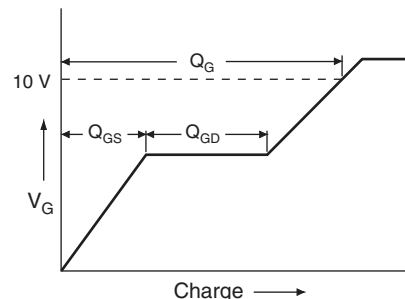
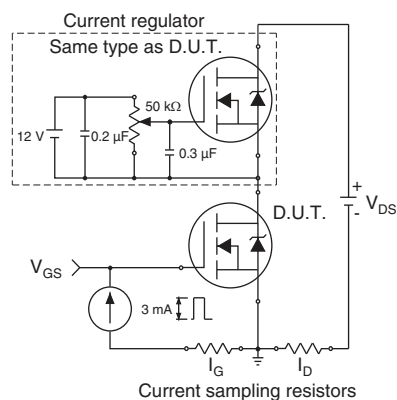


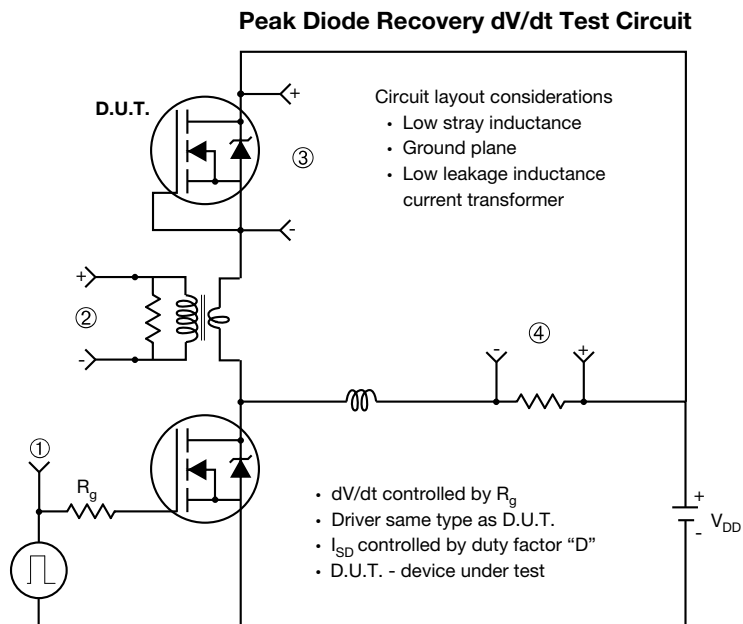
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)




Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Fig. 12d - Maximum Avalanche Energy vs. Drain Current

Fig. 13a - Basic Gate Charge Waveform

Fig. 13b - Gate Charge Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91113.

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.